

# Storage Class Memory: Learning from 3D NAND

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#### Forward-Looking Statements

This presentation contains forward-looking statements that involve risks and uncertainties, including, but not limited to, statements regarding our product and technology positioning, the anticipated benefits of our new technologies and transitioning into 3D NAND. Forward-looking statements should not be read as a guarantee of future performance or results, and will not necessarily be accurate indications of the times at, or by, which such performance or results will be achieved, if at all. Forward-looking statements are subject to risks and uncertainties that could cause actual performance or results to differ materially from those expressed in or suggested by the forward-looking statements.

Additional key risks and uncertainties include the impact of continued uncertainty and volatility in global economic conditions; actions by competitors; difficulties associated with go-to-market capabilities and transitioning into 3D NAND; business conditions; growth in our markets; and pricing trends and fluctuations in average selling prices. More information about the other risks and uncertainties that could affect our business are listed in our filings with the Securities and Exchange Commission (the "SEC") and available on the SEC's website at <a href="www.sec.gov">www.sec.gov</a>, including our and SanDisk's most recently filed periodic reports, to which your attention is directed. We do not undertake any obligation to publicly update or revise any forward-looking statement, whether as a result of new information, future developments or otherwise, except as otherwise required by law.

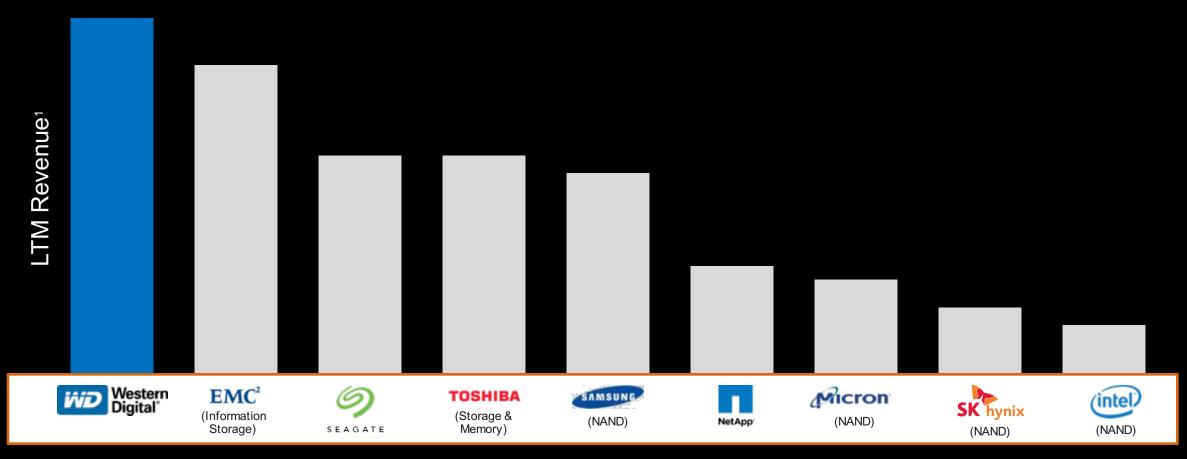
# The Western Digital Family of Brands



Bringing the Possibilities of Data to Life

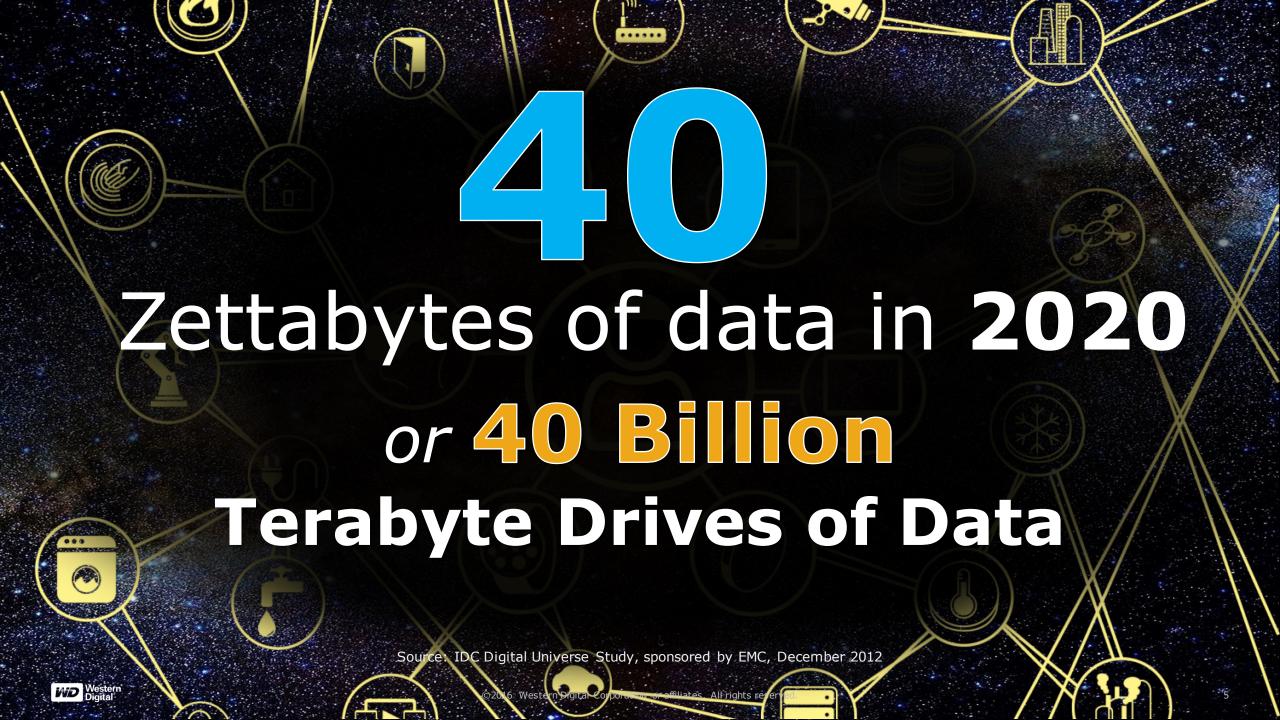


# A Global Leader in Storage Technology

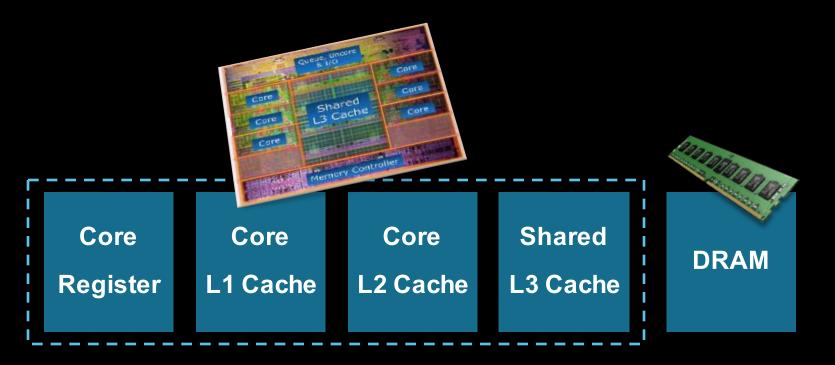


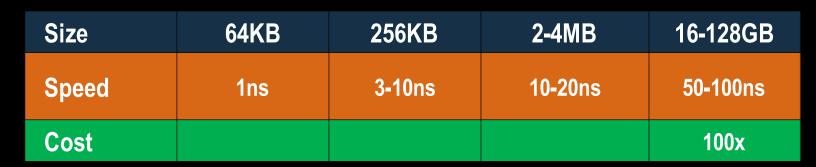
<sup>&</sup>lt;sup>1</sup> LTM revenues based on most recent public filings and Wall Street research; Western Digital and SanDisk LTM as of 4/1/2016; Toshiba represents March 2016 LTM revenue.

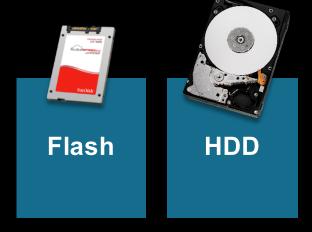




# **Moving Mountains of Data**



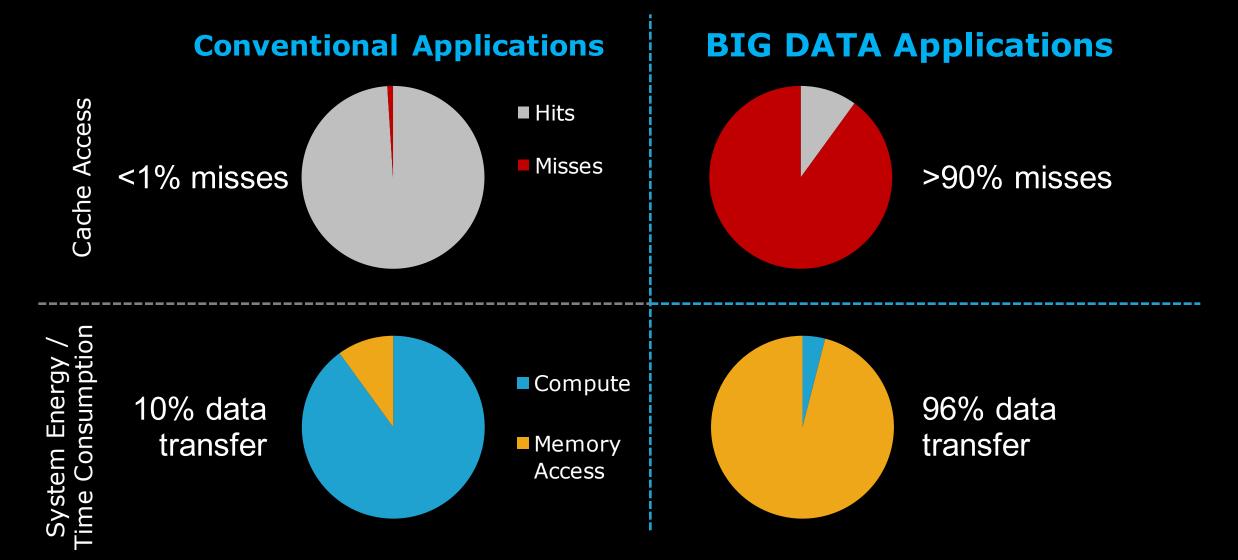




512GB-4TB	4-16TB
100,000ns <b>-</b> 2,000,000ns	5- 10,000,000ns
2,000,000118	10,000,000115
<b>5</b> x	1x



### The Data Bottleneck

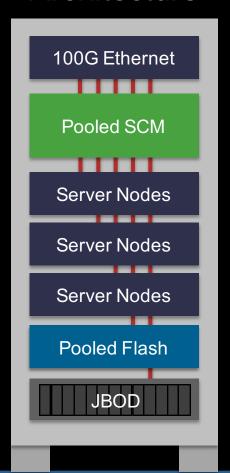




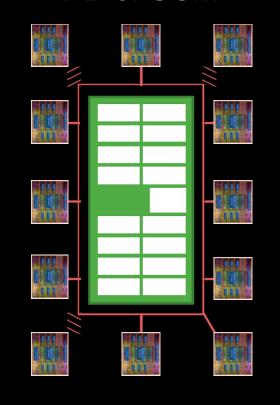
## **Data Centric Computer Architectures**

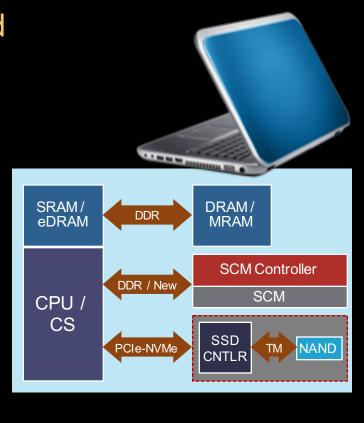


Rack Scale Architecture

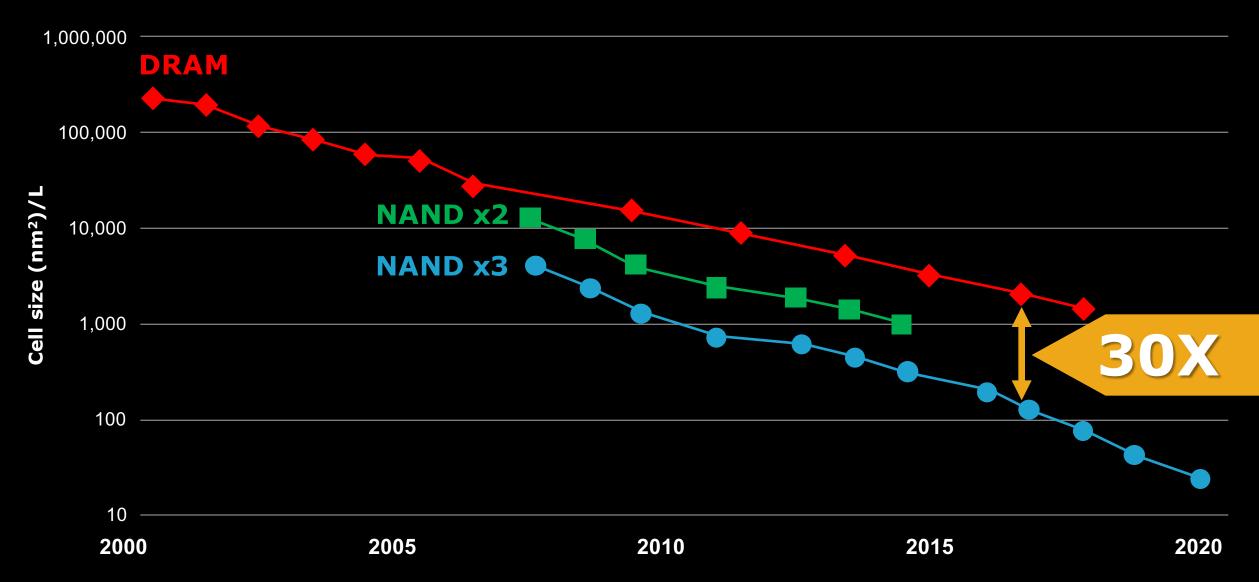


Cheap CPUs Around PB of SCM



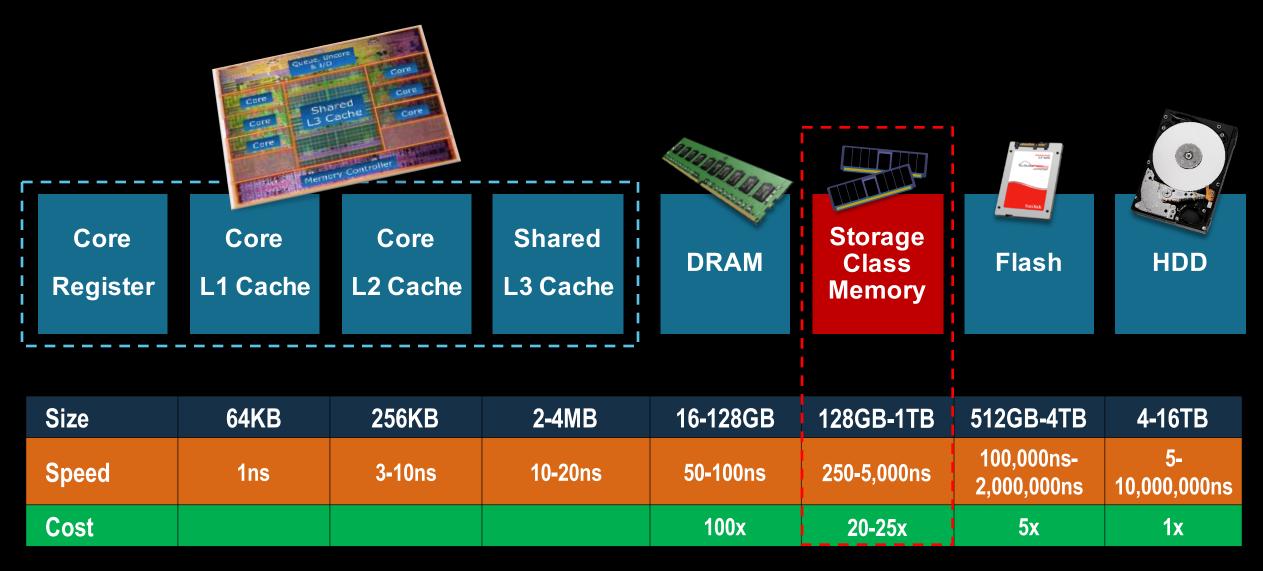


# **DRAM & NAND Cell Sizes**



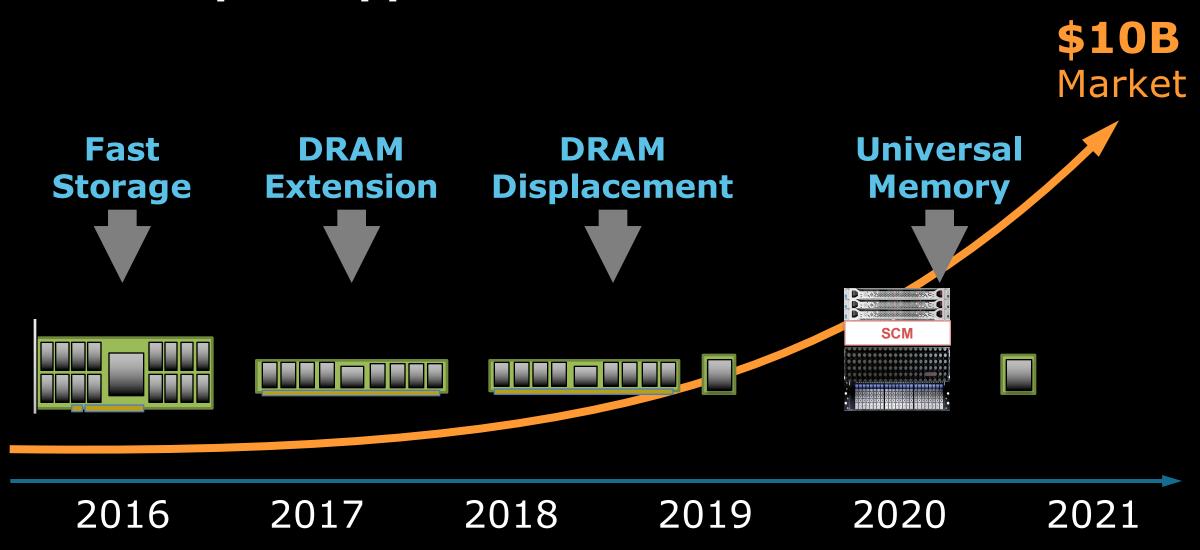


# **Moving Mountains of Data**



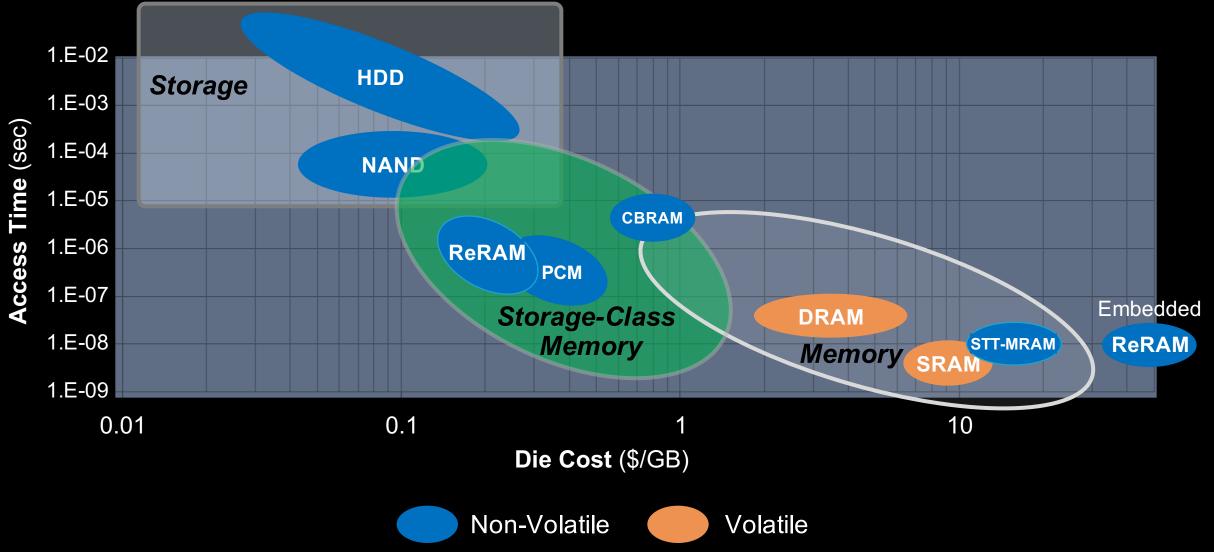


# **SCM Compute Applications / Market Evolution**





# **Memory & Storage Hierarchy**





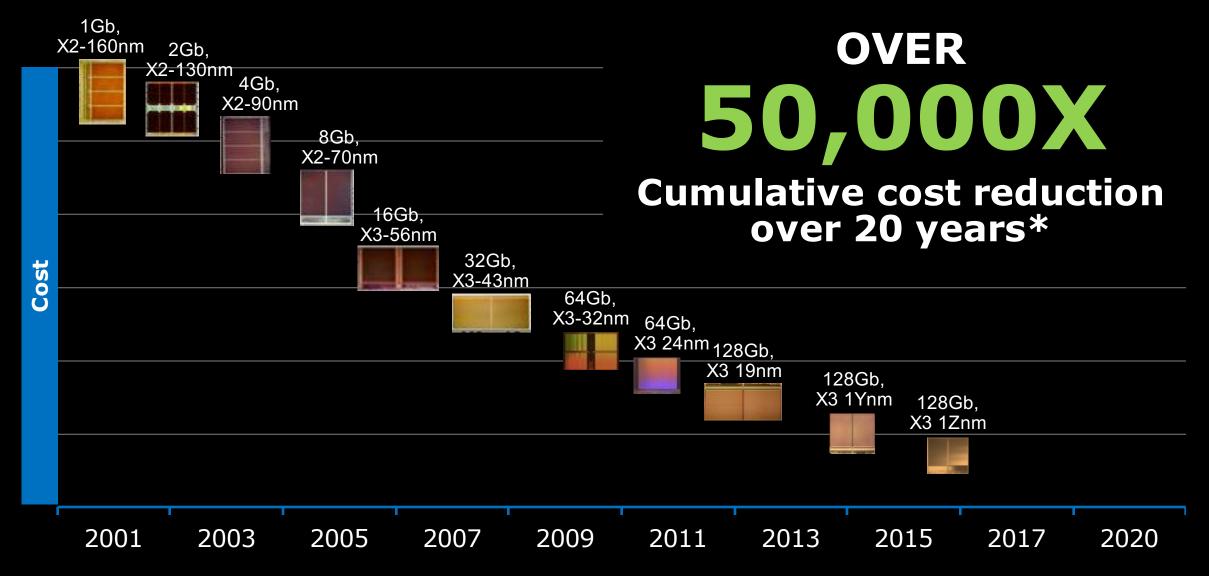
### **The FAB 4 of Semiconductor Nirvana**

Case Study
2D NAND
→ 3D NAND
Transition

# Cost Scalability Scale Ecosystem

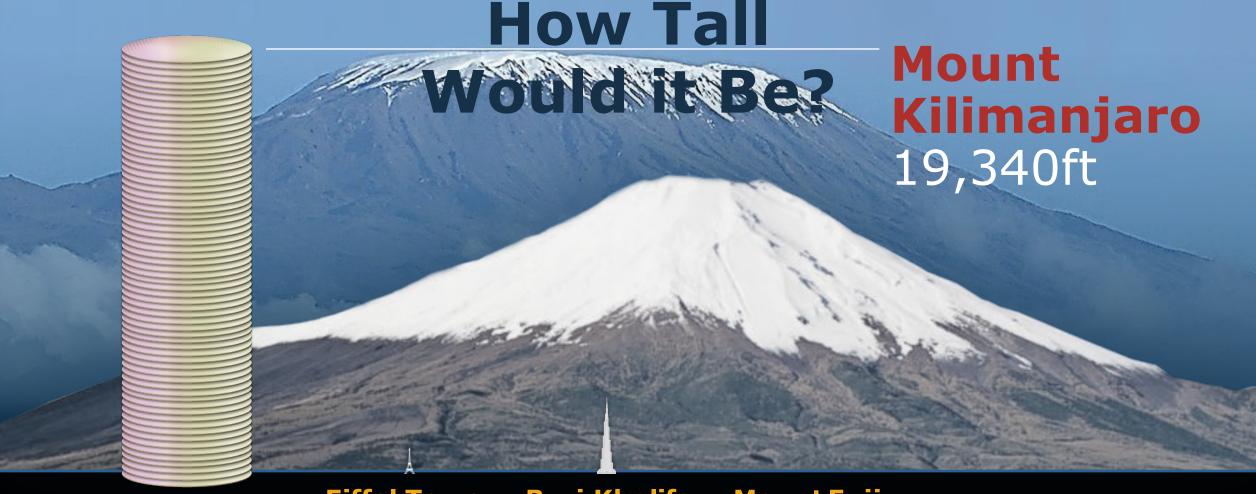


### In NAND We Trust: More than Moore





# When the Chips are Down, the Wafers are Up!



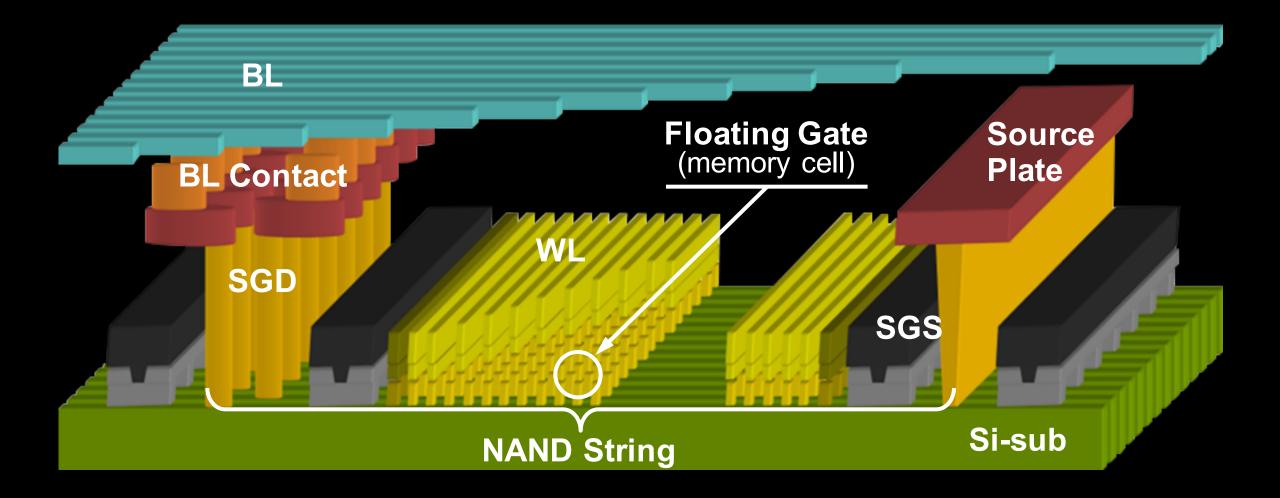
Number of wafers produced in 2016 In Yokkaichi

Eiffel Tower 984ft **Burj Khalifa** 2717ft

Mount Fuji 12,388ft



# **2D NAND Architecture**





# Case Study 2D NAND → 3D NAND Transition

# Scaling Stopped the Music for 2D NAND!

- Cost of lithography
- Density of electron storage in the floating gate
- Proximity effects from adjacent cells

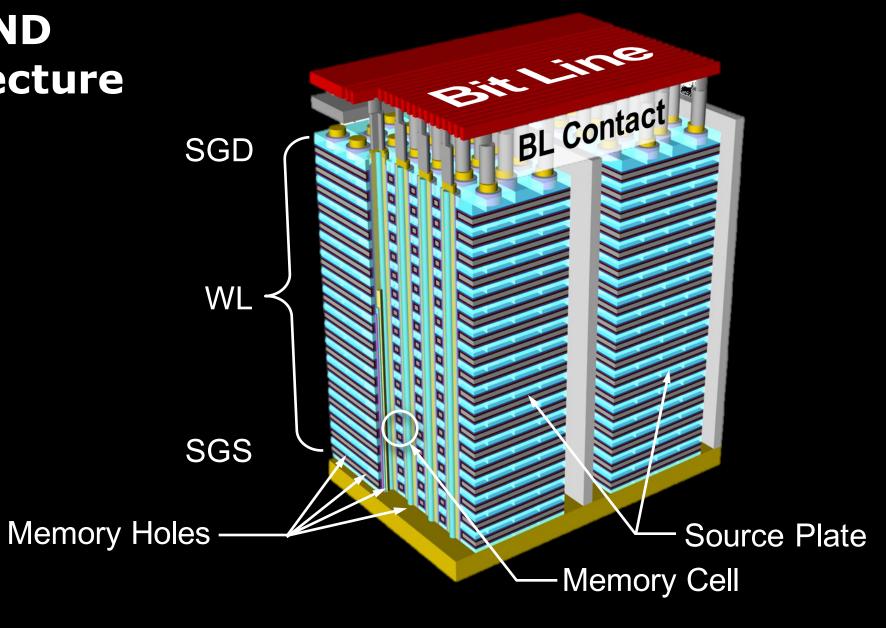
3D NAND: A necessary revolution



# **3D NAND** Cell Charge Trap Layer SG Gate **Control Gate** Poly-Si Body SG

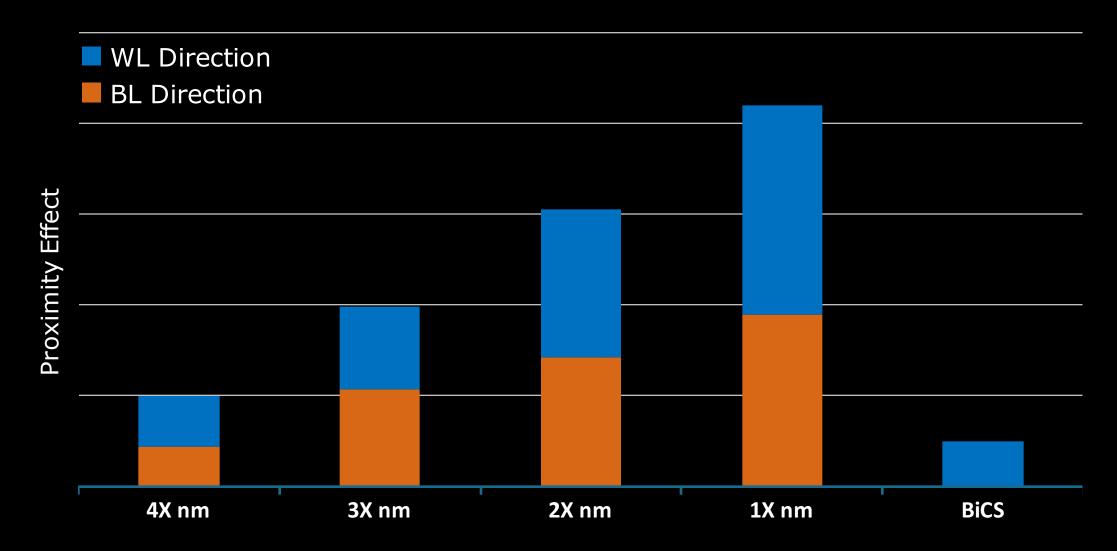


# 3D NAND Architecture





# **Proximity Effect in BiCS**





# Our Next Generation 3D NAND Technology is Here

World's first 64-layer
3D NAND architecture

Capacities up to 512Gb on a single chip

Smallest 256Gb chip in the industry

**OEM** sampling in the current quarter; retail shipments expected in calendar Q4 2016

# **NAND Cost Scaling Continues**

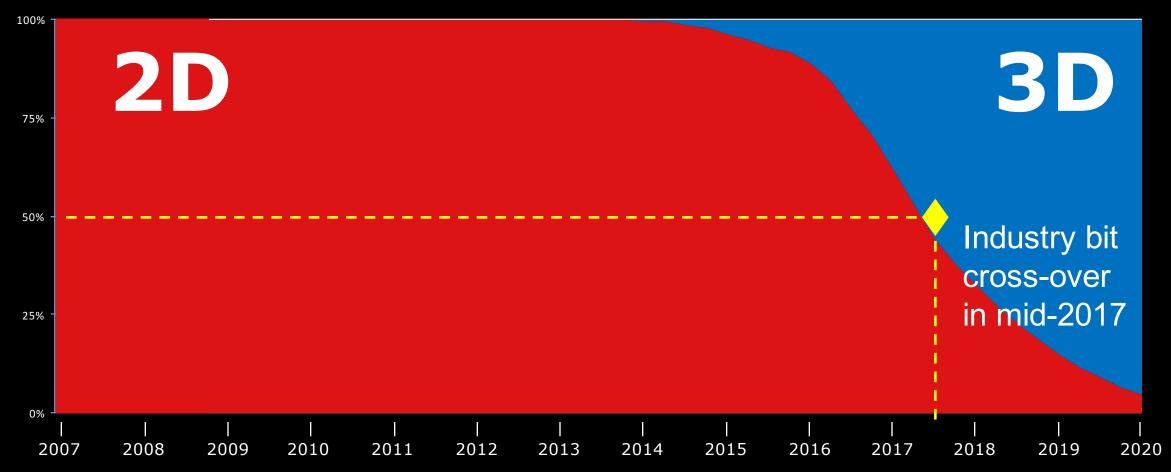


# The BiCS Scaling March 64L 48L 24L BiCS5 BiCS4 BiCS3 BiCS2 BiCS<sub>1</sub>



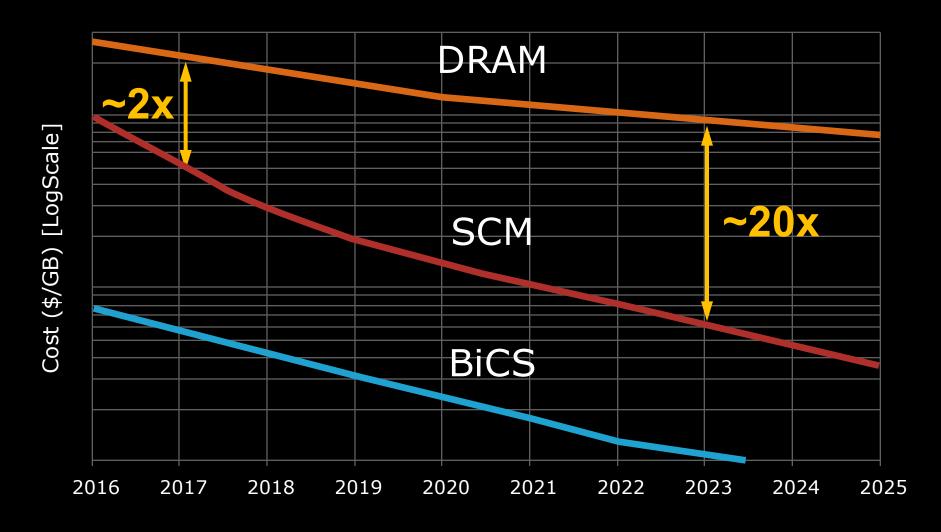
# Manufacturing Scale: Mountains of wafers being converted to 3D NAND

Industry 2D NAND vs. 3D NAND Bit Output





# **Cost Scaling for SCM Market Adoption**



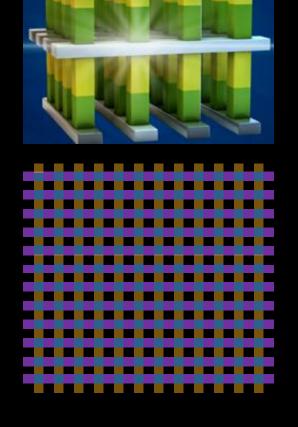
Note: Technology transition cadence assumed 18 months for all technologies ReRAM & 3DXP greenfield fabs, NAND & DRAM existing fabs



<sup>\*</sup> DRAM data source: IDC ASP forecast with 45% GM assumed \*\* 13 nm: assumes EUV @ 1.4x i-ArF capex cost, 2160 w/day

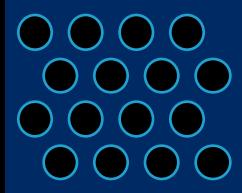
# **3D Technologies for SCM**

### 3D XPoint



### 3D NAND

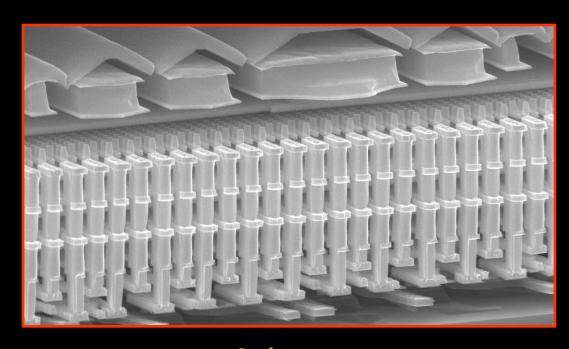




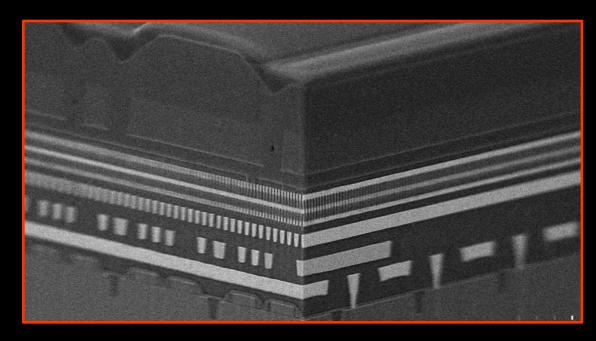
- Cell and Materials
- Selector
- Process Architecture
- Product
- Ecosystem



# **Cross Point Memory Implementations**



8-layer
3D cross-point array memory
ca. 2002



32Gb, 24nm, 2-layer 3D cross-point array ReRAM 2013



## 3D Resistive RAM as Storage Class Memory

**Latency & Endurance** 

**Lower Cost** 

Scalability with 3D

3D ReRAM

**Ecosystem Support** 

Scale & Capital Efficiency

ReRAM is Western Digital's Choice for SCM



# Summary

Western Digital + SanDisk: A leading combination

Data explosion enabled by edge devices

3D NAND:

A revolution underway

Lower latency memory component needed for data-centric computing

3D ReRAM is a scalable SCM solution





Bringing the possibilities of data to life.